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	•			· . ·	and multilayer) and adhesive) not	US-PGPUB;	2002/11/20	13.30	
	٠.				(semiconductor and (back with date) and	EPO; JPO;	1.4	. ,	l
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1	•				(438/266) or (438/311) or (438/455) or	US-PGPUB	2002/11/26	14:09	
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		12			(438/591) or (438/682-683)) CCLS.) and (back	US-PGPUB;		i i	
		of the second	1, 1, 1	** 3	with gate)	EPO; JPO;			
٠.					"Ten gate)	DERWENT;			
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- 4				525	(430/4/9)).CCES:	US-PGPUB	* :		
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	.,"				(438/479)).CCLS.) and (tungsten or W)	US-PGPUB;			
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	`				US-4335391-\$ or US-6455398-\$ or US-6429095-\$	US-PGPUB			
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			US-4335391-\$ or US-6455398-\$ or US-6429095-\$ or US-6429094-\$ or US-6417075-\$ or	US-PGPUB;	2002/11/26 15:23
			US-4335391-\$ or US-6455398-\$ or US-6429095-\$ or US-6429094-\$ or US-6417075-\$ or US-6313012-\$	US-PGPUB; EPO; JPO;	2002/11/26 15:23
			US-4335391-\$ or US-6455398-\$ or US-6429095-\$ or US-6429094-\$ or US-6417075-\$ or US-6413012-\$ or US-6306729-\$ or US-6221738-\$ or	US-PGPUB; EPO; JPO; DERWENT;	2002/11/26 15:23
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		US-4752590-\$).did. or (US-20020160603-\$ or		
.		US-20020137265-\$ or US-20020096717-\$ or		
-	1 100	US-20020094663-\$ or US-20020090798-\$ or		
		US-20020086470-\$ or US-20020086469-\$ or		
\cdot		US-20020086465-\$ or US-20020072201-5 or		
		US-20020072200-\$ or US-20020068419-\$ or		
-		US-20020048844-\$ or US-20020022344-\$ or		
1		US-20020022337-\$ or US-20010021540-\$ or		
<u> </u>		US-20010012677-\$ or US-20010002329-\$).did.)		.
.		and SOI and (tungsten or W)		
	12	(((US-6362078-\$ or US-6057212-\$ or	1	
		US-4335391-\$ or US-6455398-\$ or US-6429095-\$	USPAT;	2002/11/26 15:30
		or US-6429094-\$ or US-6417075-\$ or	US-PGPUB;	
.		US-6410436-\$ or US-6333202-\$ or US-6313012-\$	EPO; JPO;	
		or US-6306729-\$ or US-6221738-\$ or	DERWENT;	
Ŧ		US-6150031 c on UG 6146080 t	IBM_TDB	
: .		US-6150031-\$ or US-6146979-\$ or US-6143628-\$		
. [or US-6121112-\$ or US-6103598-\$ or US-610300000000000000000000000000000000000		
-		US-6103009-\$ or US-6100165-\$ or US-6054363-\$		
		or US-6045626-\$, or US-5985739-\$ or		
		US-5966620-\$ or US-5937312-\$ or US-5856229-\$		
		or US-5773355-\$).did. or (US-5670411-\$ or		
		US-5536361-\$ or US-5492859-\$ or US-5466631-\$		
		or US=5453394-\$ or US-5439843-\$ or		
		US-5399231-\$ or US-5395481-\$ or US-5391257-\$		
1.		or US-5387555-\$ or US-5374581-\$ or		
1		US-5374329-\$ or US-5371037-\$ or US-5366924-\$		
		or US-5324678-\$ or US-5310446-\$ or		
		US-5308776-\$ or US-5277748-\$ or US-5258322-\$		
- 1	1	or US-5244817-\$ or US-5250460-\$ or		
		or US-5244817-\$ or US-5250460-\$ or US-5098861-\$		
		or US-5244817-\$ or US-5250460-\$ or US-5229305-\$ or US-5168078-\$ or US-5098861-\$ or US-4829018-\$ or US-4826787-\$ or		
		or US-5244817-\$ or US-5250460-\$ or US-5229305-\$ or US-5168078-\$ or US-5098861-\$ or US-4829018-\$ or US-4826787-\$ or US-4752590-\$).did. or (US-20020160603-\$ or		
		or US-5244817-\$ or US-5250460-\$ or US-5229305-\$ or US-5168078-\$ or US-5098861-\$ or US-4829018-\$ or US-4826787-\$ or US-4752590-\$).did. or (US-20020160603-\$ or US-20020137265-\$ or US-20020096717-\$ or		
		or US-5244817-\$ or US-5250460-\$ or US-5229305-\$ or US-5168078-\$ or US-5098861-\$ or US-4829018-\$ or US-4826787-\$ or US-4752590-\$).did. or (US-20020160603-\$ or US-20020137265-\$ or US-20020096717-\$ or US-20020094663-\$ or US-20020094798-\$ or		
		or US-5244817-\$ or US-5250460-\$ or US-5229305-\$ or US-5168078-\$ or US-5098861-\$ or US-4829018-\$ or US-4826787-\$ or US-4752590-\$).did. or (US-20020160603-\$ or US-20020137265-\$ or US-20020096717-\$ or US-20020094663-\$ or US-20020086469-\$ or US-20020086470-\$ or US-20020086469-\$ or		
		or US-5244817-\$ or US-5250460-\$ or US-5229305-\$ or US-5168078-\$ or US-5098861-\$ or US-4829018-\$ or US-4826787-\$ or US-4752590-\$).did. or (US-20020160603-\$ or US-20020137265-\$ or US-20020096717-\$ or US-20020094663-\$ or US-20020086469-\$ or US-20020086470-\$ or US-20020086469-\$ or		
		or US-5244817-\$ or US-5250460-\$ or US-5229305-\$ or US-5168078-\$ or US-5098861-\$ or US-4829018-\$ or US-4826787-\$ or US-4752590-\$).did. or (US-20020160603-\$ or US-20020137265-\$ or US-20020096717-\$ or US-20020094663-\$ or US-20020090798-\$ or US-20020086469-\$ or US-20020086469-\$ or US-20020086465-\$ or US-20020072201-\$ or		
		or US-5244817-\$ or US-5250460-\$ or US-5229305-\$ or US-5168078-\$ or US-5098861-\$ or US-4829018-\$ or US-4826787-\$ or US-4752590-\$).did. or (US-20020160603-\$ or US-20020137265-\$ or US-20020096717-\$ or US-20020094663-\$ or US-20020090798-\$ or US-20020086470-\$ or US-20020086469-\$ or US-20020086465-\$ or US-20020072201-\$ or US-20020072200-\$ or US-20020072200-\$		
		or US-5244817-\$ or US-5250460-\$ or US-5229305-\$ or US-5168078-\$ or US-5098861-\$ or US-4829018-\$ or US-4826787-\$ or US-4752590-\$).did. or (US-20020160603-\$ or US-20020094663-\$ or US-20020096717-\$ or US-20020094663-\$ or US-20020090798-\$ or US-20020086469-\$ or US-20020072201-\$ or US-20020072200-\$ or US-20020072201-\$ or US-20020048844-\$ or US-2002022344-\$ or US-20020048844-\$ or US-2002022344-\$ or		
		or US-5244817-\$ or US-5250460-\$ or US-5229305-\$ or US-5168078-\$ or US-5098861-\$ or US-4829018-\$ or US-4826787-\$ or US-4752590-\$).did. or (US-20020160603-\$ or US-20020137265-\$ or US-20020096717-\$ or US-20020094663-\$ or US-20020096798-\$ or US-20020086469-\$ or US-20020086469-\$ or US-20020086465-\$ or US-20020072201-\$ or US-20020072201-\$ or US-20020048844-\$ or US-2002002344-\$ or US-20020022337-\$ or US-20010021540-\$ or US-20020022337-\$ or US-20010021540-\$ or		*
		or US-5244817-\$ or US-5250460-\$ or US-5229305-\$ or US-5168078-\$ or US-5098861-\$ or US-4829018-\$ or US-4826787-\$ or US-4752590-\$).did. or (US-20020160603-\$ or US-20020137265-\$ or US-20020096717-\$ or US-20020094663-\$ or US-20020096798-\$ or US-20020086469-\$ or US-20020086469-\$ or US-20020072201-\$ or US-20020072007201-\$ or US-200200720072007200720072007200720072007		
		or US-5244817-\$ or US-5250460-\$ or US-5229305-\$ or US-5168078-\$ or US-5098861-\$ or US-4829018-\$ or US-4826787-\$ or US-4752590-\$).did. or (US-20020160603-\$ or US-20020137265-\$ or US-20020096717-\$ or US-20020094663-\$ or US-20020090798-\$ or US-20020086469-\$ or US-20020086469-\$ or US-20020072201-\$ or US-20020072001-\$ or US-20020072201-\$ or US-20020072001-\$ or US-20020072201-\$ or US-20020072000000000000000000000000000000		
		or US-5244817-\$ or US-5250460-\$ or US-5229305-\$ or US-5168078-\$ or US-5098861-\$ or US-4829018-\$ or US-4826787-\$ or US-4752590-\$).did. or (US-20020160603-\$ or US-20020137265-\$ or US-20020096717-\$ or US-20020094663-\$ or US-20020090798-\$ or US-20020086469-\$ or US-20020086465-\$ or US-20020072201-\$ or US-20020072344-\$ or US-20020022344-\$ or US-20010012677-\$ or US-20010021540-\$ or US-20010012677-\$ or US-20010021540-\$ or US-20010012677-\$ or US-2001002329-\$).did.) and SOI and (tungsten or W) and silicide semiconductor and ((tungsten or W) same	USPAT;	2002/11/26 15:32
		or US-5244817-\$ or US-5250460-\$ or US-5229305-\$ or US-5168078-\$ or US-5098861-\$ or US-4829018-\$ or US-4826787-\$ or US-4752590-\$).did. or (US-20020160603-\$ or US-20020137265-\$ or US-20020096717-\$ or US-20020094663-\$ or US-20020090798-\$ or US-20020086469-\$ or US-20020086465-\$ or US-20020072201-\$ or US-20020072200-\$ or US-20020068419-\$ or US-20020048844-\$ or US-2002002344-\$ or US-2002002337-\$ or US-20010021540-\$ or US-20010012677-\$ or US-20010002329-\$).did.) and SOI and (tungsten or W) and silicide semiconductor and (tungsten or W) same silicide same UHV same deportion same	US-PGPUB;	2002/11/26 15:32
		or US-5244817-\$ or US-5250460-\$ or US-5229305-\$ or US-5168078-\$ or US-5098861-\$ or US-4829018-\$ or US-4826787-\$ or US-4752590-\$).did. or (US-20020160603-\$ or US-20020137265-\$ or US-20020096717-\$ or US-20020094663-\$ or US-20020090798-\$ or US-20020086469-\$ or US-20020086465-\$ or US-20020072201-\$ or US-20020072200-\$ or US-20020072201-\$ or US-20020072200-\$ or US-2002002344-\$ or US-2002002337-\$ or US-20010021540-\$ or US-2002002337-\$ or US-20010021540-\$ or US-20010012677-\$ or US-20010002329-\$).did.) and SOI and (tungsten or W) and silicide semiconductor and ((tungsten or W) same silicide same UHV same deporption same (silane or "SiH.sub.4") same (ammonia or	US-PGPUB; EPO; JPO;	2002/11/26 15:32
		or US-5244817-\$ or US-5250460-\$ or US-5229305-\$ or US-5168078-\$ or US-5098861-\$ or US-4829018-\$ or US-4826787-\$ or US-4752590-\$).did. or (US-20020160603-\$ or US-20020137265-\$ or US-20020096717-\$ or US-20020094663-\$ or US-20020090798-\$ or US-20020086469-\$ or US-20020086465-\$ or US-20020072201-\$ or US-20020072200-\$ or US-20020068419-\$ or US-20020048844-\$ or US-2002002344-\$ or US-2002002337-\$ or US-20010021540-\$ or US-20010012677-\$ or US-20010002329-\$).did.) and SOI and (tungsten or W) and silicide semiconductor and (tungsten or W) same silicide same UHV same deportion same	US-PGPUB; EPO; JPO; DERWENT;	2002/11/26 15:32
	- 0	or US-5244817-\$ or US-5250460-\$ or US-5229305-\$ or US-5168078-\$ or US-5098861-\$ or US-4829018-\$ or US-4826787-\$ or US-4752590-\$).did. or (US-20020160603-\$ or US-20020137265-\$ or US-20020096717-\$ or US-20020094663-\$ or US-20020090798-\$ or US-20020086470-\$ or US-20020086469-\$ or US-20020086465-\$ or US-20020072201-\$ or US-20020072200-\$ or US-20020068419-\$ or US-20020048844-\$ or US-2002002344-\$ or US-2002002337-\$ or US-20010021540-\$ or US-20010012677-\$ or US-20010002329-\$).did.) and SOI and (tungsten or W)) and silicide semiconductor and ((tungsten or W) same silicide same UHV same deporption same (silane or "SiH.sub.4") same (āmmonia or "NH.sub.3"))	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
	- 0	or US-5244817-\$ or US-5250460-\$ or US-5229305-\$ or US-5168078-\$ or US-5098861-\$ or US-4829018-\$ or US-4826787-\$ or US-4752590-\$).did. or (US-20020160603-\$ or US-20020096717-\$ or US-20020094663-\$ or US-20020096717-\$ or US-20020086469-\$ or US-20020086465-\$ or US-20020072201-\$ or US-20020086465-\$ or US-20020072201-\$ or US-20020072001-\$ or US-2002007239-\$).did.) and SOI and (tungsten or W) and silicide semiconductor and ((tungsten or W) same silicide same UHV same deporption same (silane or "SiH.sub.4") same (ammonia or "NH.sub.3"))	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2002/11/26 15:32
	- 0	or US-5244817-\$ or US-5250460-\$ or US-5229305-\$ or US-5168078-\$ or US-5098861-\$ or US-4829018-\$ or US-4826787-\$ or US-4752590-\$) .did. or (US-20020160603-\$ or US-20020034663-\$ or US-20020096717-\$ or US-20020094663-\$ or US-20020090798-\$ or US-20020086469-\$ or US-20020086469-\$ or US-20020072201-\$ or US-20020072200-\$ or US-20020072201-\$ or US-20020072200-\$ or US-200200724-\$ or US-20020048844-\$ or US-20020022344-\$ or US-20020022337-\$ or US-20010021540-\$ or US-20020022337-\$ or US-2001002329-\$).did.) and SOI and (tungsten or W) and silicide semiconductor and ((tungsten or W) same silicide same UHV same deporption same (silane or "SiH.sub.4") same (ammonia or "NH.sub.3")) semiconductor and ((tungsten or W) same silicide same (silane or "SiH.sub.4") same	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB;	
	- 0	or US-5244817-\$ or US-5250460-\$ or US-5229305-\$ or US-5168078-\$ or US-5098861-\$ or US-4829018-\$ or US-4826787-\$ or US-4752590-\$).did. or (US-20020160603-\$ or US-20020096717-\$ or US-20020094663-\$ or US-20020096717-\$ or US-20020086469-\$ or US-20020086465-\$ or US-20020072201-\$ or US-20020086465-\$ or US-20020072201-\$ or US-20020072001-\$ or US-2002007239-\$).did.) and SOI and (tungsten or W) and silicide semiconductor and ((tungsten or W) same silicide same UHV same deporption same (silane or "SiH.sub.4") same (ammonia or "NH.sub.3"))	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	
	- 0	or US-5244817-\$ or US-5250460-\$ or US-5229305-\$ or US-5168078-\$ or US-5098861-\$ or US-4829018-\$ or US-4826787-\$ or US-4752590-\$) .did. or (US-20020160603-\$ or US-20020034663-\$ or US-20020096717-\$ or US-20020094663-\$ or US-20020090798-\$ or US-20020086469-\$ or US-20020086469-\$ or US-20020072201-\$ or US-20020072200-\$ or US-20020072201-\$ or US-20020072200-\$ or US-200200724-\$ or US-20020048844-\$ or US-20020022344-\$ or US-20020022337-\$ or US-20010021540-\$ or US-20020022337-\$ or US-2001002329-\$).did.) and SOI and (tungsten or W) and silicide semiconductor and ((tungsten or W) same silicide same UHV same deporption same (silane or "SiH.sub.4") same (ammonia or "NH.sub.3")) semiconductor and ((tungsten or W) same silicide same (silane or "SiH.sub.4") same	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB;	

				2	•
	1 .		semiconductor and ((tungsten or W) same	USPAT;	2002/11/26 15:41
			silicide same UHV same desorption same	US-PGPUB;	2002/11/20 13.41
			(silane or "SiH.sub.4") same (ammonia or	EPO; JPO;	
•			"NH.sub.3"))	DERWENT;	
		• .		IBM TDB	1
•			semiconductor and ((tungsten with silicide)	USPAT;	2002/11/26 15:42
		7, 4	or (WSi or WSiN)).ti. and silane and ammonia	US-PGPUB;	2002/11/26 15:42
				EPO; JPO;	
	0			DERWENT;	
		1 0 1		IBM TDB	
	**	2	semiconductor and ((WSiN) same silane same	USPAT;	2002/11/26 15:45
			ammonia)	US-PGPUB;	2002/11/26 15:45
				EPO; JPO;	
	1.1.			DERWENT:	
				IBM TDB	
	- '	2518	semiconductor and (nitrid\$6 same tungsten	USPAT;	2002/11/26 15:48
			adj silicide)	US-PGPUB;	2002/11/26 15:48
·				EPO; JPO;	
				DERWENT;	
				IBM TDB	1
	-	411	(semiconductor and (nitrid\$6 same tungsten	USPAT;	2002/11/26 15 56
			adj silicide)) and silane	US-PGPUB;	2002/11/26 15:56
:				EPO; JPO;	
				DERWENT;	
				IBM TDB	
	j - 3 - 3 - 3 - 3	146	((semiconductor and (nitrid\$6 same tungsten	USPAT;	2002/11/06 15:50
-			adj silicide)) and silane) and ammonia	US-PGPUB;	2002/11/26 15:52
	·		and briancy drie diminority		
				EPO; JPO;	1
				DERWENT;	
	- ' :	. 6	semiconductor and (monolayer with (tungsten	IBM_TDB	Same and the same of
• [adj silicide))	USPAT;	2002/11/26 15:56
ı			adj bilicide//	US-PGPUB;	
				EPO; JPO;	
		*		DERWENT;	- 8- 3
	<u>=</u>	0	(semiconductor and (monolayer with (tungsten	IBM_TDB	
ĺ	*		adj silicide))) and silane	USPAT;	2002/11/26 15:56
1			and straine	US-PGPUB;	
ſ				EPO; JPO;	
1				DERWENT;	
		1	((semiconductor and (nitrid\$6 same tungsten	IBM_TDB	
			adj silicide)) and silane) and nitrad\$6 *	USPAT;	2002/11/26 16:31
1			day bilicide// and silane/ and nitrads6 4	US-PGPUB;	
1	•			EPO; JPO;	
				DERWENT;	
	-	92	semiconductor and (electroplating same	IBM_TDB	0000/0-/-
			electrolessly)	USPAT;	2002/11/26 16:32
		1		US-PGPUB;	1.
				EPO; JPO;	*
				DERWENT;	
	2	54	semiconductor and (electroplating with	'IBM_TDB	
1.			electrolessly)	USPAT;	2002/11/26 16:35
-	4		, and a second s	US-PGPUB;	
	•			EPO; JPO;	
1				DERWENT;	
	<u>- 1 </u>		semiconductor and (electroplating with	IBM_TDB	
			electrolessly with equivalent)	USPAT;	2002/11/26 16:35
			crectoressty with equivalent)	US-PGPUB;	·
				EPO; JPO;	
1	- 1	12.5		DERWENT;	
1		69	semiconductor and SOI and (wafer with	IBM_TDB	
	1		bond\$4) and (tungator or th) ()	USPAT;	2003/05/23 11:24
.	.		bond\$4) and (tungsten or W) and (adhesive or gluing) and passivat\$4	US-PGPUB;	
			5-wind passivals4	EPO; JPO;	- - -
		×		DERWENT;	
1	- :	19	semi conductor and (back in the	IBM_TDB	×
		"	semiconductor and (back with gate) and	USPAT;	2003/05/23 13:54
			(wafer with bond\$4) and (tungsten or W) and (adhesive or gluing) and passivat\$4	US-PGPUB;	
			, admostve of gruing) and passivats4	EPO; JPO;	
			•	DERWENT;	
_		<u> </u>	the state of the s	IBM_TDB	

		. g				141	* 0=
	-]		1 (back adj gate) and LTO and SOI	TIODAM	11 0000 /00 /00
	1				tousing and gate, and bio and soi	USPAT;	2003/11/10 14:36
		•		:		US-PGPUB;	
			ŀ			EPO; JPO;	
		-	1			DERWENT;	
		•	1		5 (back adi gate) and two	IBM_TDB	
			1	7	(back adj gate) and LTO	USPAT;	2003/11/10 14:36
						US-PGPUB;	
1	1' .		-			EPO; JPO;	
	1	Α,				DERWENT;	
		•		*		IBM TDB	
				291	semiconductor and (gate and lift adj off)	USPAT;	2003/11/12 15:49
					Sant and IIIs day off,		2003/11/12 15:49
	,	· • ;	1.			US-PGPUB;	
		-				EPO; JPO;	
				.e.,		DERWENT;	
			1	22	(Semiconductor and Jack and life all sex	IBM_TDB	
		*			(semiconductor and (gate and lift adj off)) and LTO	USPAT;	2003/11/12 16:07
				1	and hio	US-PGPUB;	
			1.			EPO; JPO;	
						DERWENT;	
			**			IBM TDB	
	:	- ' · · · ·	1.	. 2	("6238737").PN.	USPAT;	2003/11/12 16:20
						US-PGPUB;	12, 12, 10.20
			ľ·	-00-		EPO; JPO;	. *-
	.	., .,				DERWENT;	
	,					IBM TDB	
	-		. "	253	semiconductor and metal and silicide and LTO		0000/10/10 10 11
	,	1			and (siN or polysilicon or (amorphous with	USPAT;	2003/11/13 10:51,
	, t				silicon))	US-PGPUB;	
		1	. 3			EPO; JPO;	
		٠				DERWENT;	
٠	<u>.</u> .			, 2	("6238737").PN.	IBM_TDB	
				4	("6238/3/").PN.	USPAT;	2003/11/13 14:17
`		2.1	1.2			US-PGPUB;	
			١.			EPO; JPO;	
-						DERWENT;	· · · · · · · · · · · · · · · · · · ·
۱.				٧		IBM TDB	
-	. = .			- 0	(("6238737").PN.) and (glue or gluing or	USPAT;	2003/11/13 14:17
.			,		glueing)	US-PGPUB;	2003/11/13 14:1/
-				4		EPO; JPO;	, ,
		· - · ·				DERWENT;	
-				h		1	
-	' '			0	((("6238737").PN.) and (glue or gluing or	IBM_TDB	
-	2				glueing)) and ((amorphous adj silicon) or "a	USPAT;	2003/11/13 14:18
·	1	100		8	Si" or SiN or (silicon ādj nitride))	US-PGPUB;	
1	,	-		2 m yr 2 m	or or sin or (silicon adj nitride))	EPO; JPO;	
-				· ',		DERWENT;	
1	±1.			1 - 0	/// ((6)2072711) PM) 3 (2)	IBM_TDB	1
			7.00		((("6238737").PN.) and (glue or gluing or	USPAT;	2003/11/13 15:19
	•	1		*	glueing)) and ((amorphus adj silicon) or "a	US-PGPUB;	
1					Si" or SiN or (silicon adj nitride))	EPO; JPO;	
	* .		*	٠.		DERWENT;	
	,	· ·				IBM_TDB	
	7.00			. 1		USPAT;	2003/11/13 15:21
	,		1.		or glueing or adhesive or bonding) same (SiN	US-PGPUB;	= 0,0,11,13 13,21 ,
1	•				or silicon)) and passivat\$4	EPO; JPO;	
			• .			DERWENT;	
	٠.	I				IBM_TDB	
	÷. •	. 1		25	(back adj gate) and (gate adj oxide) and	USPAT;	2002/22/20
1	· .	1			((glue or gluing or glueing or adhesive or		2003/11/13 15:22
	· • •		. • • •		bonding) same (SiN or silicon)) and	US-PGPUB;	-
			· .		passivat\$4	EPO; JPO;	
			•		#	DERWENT;	
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USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;			. ,	.				DERWENT;	
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US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; EPO; JPO; DERWENT;	ŀ			i		331	(back adj gate).tl.	USPAT;	2003/11/13 20:46
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140 semiconductor and SOI and gate and (refractory) and passivation EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;					•		(double adj gate) and (back adj gate))		2003/11/13 20:49
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	,			and (refractory) and passivation	US-PGPUB;	1 - 5 , 5 , 5 , 5 , 5	,
					EPO; JPO;		. 0
		2		700	DERWENT;	•	
			: · . •		IBM_TDB		·×
	-		88		USPAT;	2003/11/13	20:55
	·			and ((refractory) same (barrier or	US-PGPUB;		
	,			passivation))	EPO; JPO;		
			``		DERWENT;		
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	-		27		USPAT;	2003/11/13	21:15
-				(gate adjl oxide) and ((refractory) same	US-PGPUB;		
				(barrier or passivation))	EPO; JPO;) -	•
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				semiconductor and (COT add auto-	IBM_TDB		
			. , ,	semiconductor and (SOI adj substrate) and, (gate adj1 oxide) and ((refractory) same	USPAT;	2003/11/13	21:24
			1 2	(barrier or passivation)) and (second adj	US-PGPUB;		4.7
				substrate)	EPO; JPO;		
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.	- ' . '		2	semiconductor and (SOI adj substrate) and	IBM_TDB USPAT;	2002/11/12	21.20
				(back adj1 gate adj1 oxide) and (refractory	US-PGPUB;	2003/11/13	.21,:29
			٠	or W or Tungsten or Ti or Titanium) and	EPO; JPO;		-
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				(off)	US-PGPUB;	-, -, -, -, -, -, -, -, -, -, -, -, -, -	Ģ2.30
-					EPO; JPO;		
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			561	In a management and a contract of the contract	IBM_TDB		
	•		701	(semiconductor and (substrate with lift adjoff)) and gate\$1	USPAT;	2003/11/13.	21:30
	tri je si			ori// did gatesi	US-PGPUB; EPO; JPO;		
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	-		62		USPAT;	2003/11/13	21:32
				off)) and gate\$1) and (gate adj oxide)	US-PGPUB;	10	
	10	,			EPO; JPO;	. •	
					DERWENT;		
			1902	(438/622).CCLS.	IBM_TDB	0000/10/10	<u> </u>
		, , ,		(130) 022) . CCIIS.	USPAT; US-PGPUB;	2003/11/13	21:34
	·		•		EPO; JPO;		,
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	÷		.678	((438/622):CCLS.) and ((second with	USPAT;	2003/11/13	21:34
		1	()	substrate) or (handle with wafer))	US-PGPUB;		
1		1	*		EPO; JPO;		
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	<u>.</u>		1	((438/622).CCLS.) and ((handle with wafer))	IBM.TDB	2002/44/	
		'	• : -	(((((((((((((((((((USPAT; US-PGPUB;	2003/11/13	∠1:35
	10 ·				EPO; JPO;		
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1	- .		2171	semiconductor and (handle with wafer)	USPAT;	2003/11/13	21:35
				× *	US-PGPUB;		
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1	_		13	(semiconductor and (handle with wafer)) and	IBM_TDB	0000/10/10	
	4			(back adj1 gate)	USPAT; US-PGPUB;	2003/11/13	21:37
		+:.	7		EPO; JPO;	* **	
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1	-		494	(semiconductor and (handle with wafer)) and	USPAT;	2003/11/13 2	21:38
-				(thin adj film)	US-PGPUB;		
1					EPO; JPO;	• '	
	• • 600	1.			DERWENT;	7	
٠,		1			IBM_TDB		

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-	194	((semiconductor and (handle with wafer)) and	USPAT;	2003/11/13 21:52
		(thin adj film)) and (gate with oxide)	US-PGPUB;	•
1.			EPO; JPO;	1
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	220		IBM_TDB	
	832	semiconductor and (handle adj1 wafer)	USPAT;	2003/11/13 21:52
	*		US-PGPUB;	
*			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
	276	(semiconductor and (handle adj1 wafer)) and	USPAT;	2003/11/13 21:52
	1	SOI	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	66		IBM_TDB	
	97.	1 (The man of the land (March) / and	USPAT;	2003/11/13 21:52
	·	SOI) and gate	US-PGPUB;	
			EPO; JPO;	
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	65	1112 and maked the same of the	IBM_TDB	
	65	(((semiconductor and (handle adj1 wafer))	USPAT;	2003/11/13 21:53
		and SOI) and gate) not (((semiconductor and	US-PGPUB;	
4 4		(handle with wafer)) and (thin adj film))	EPO; JPO;	
		and (gate with oxide))	DERWENT;	
	1-	dillond sandrania and or to	IBM_TDB	
	45		USPAT;	2003/11/13 21:53
		and SOI) and gate) not (((semiconductor and	US-PGPUB;	
*		(handle with wafer)) and (thin adj film))	EPO; JPO;	
	χ.	and (gate with oxide))) and (refractive or	DERWENT;	
_	14	tungsten or w)	IBM_TDB	
	14	(back adj gate) and (LTO or (low with	USPAT;	2004/05/14 10:08
		temperature with oxide)) and (passivation or	US-PGPUB;	1
		adhesive or gluing)	EPO; JPO;	
			DERWENT;	
_ 32		(back add care) and (man-d-led)	IBM_TDB	
	· ·	(back adj gate) and (passivation or adhesive	USPAT;	2004/05/14 10:09
		or gluing) and ((gluing or adhesi\$5) with	US-PGPUB;	
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			DERWENT;	7.0
a et attende	0	(back adj gate) and (passivation or adhesive	IBM_TDB	Soot (sá ta a sa issa
		or gluing) and (intermediate with (amorphous	USPAT;	2004/05/14 10:10
		or SiN or nitride) with situ)	US-PGPUB;	
		or principal, with Situ	EPO; JPO; DERWENT;	
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=	4	(back adj gate) and (passivation or adhesive	USPAT;	2004/05/14 10:11
	[]	or gluing) and ((amorphous or SiN or	US-PGPUB;	2004/03/14 10:11
		nitride) with situ)	EPO; JPO;	
•			DERWENT;	
· '			IBM TDB	* *
	² 0	(back adj gate) and (lift with off) and	USPAT;	2004/05/14 10:11
• • • •		((amorphous or SiN or nitride) with situ)	US-PGPUB;	7001/03/14 TO 11
			EPO; JPO;	
			DERWENT;	, [
			IBM TDB	
<u> </u>	Ó	("back-gate") and (lift with off) and	USPAT;	2004/05/14 10:11
. 0		((amorphous or SiN or nitride) with situ)	US-PGPUB:	
			EPO; JPO;	
•			DERWENT;	
			IBM TDB	
-	3	(metal with back with gate) and ((amorphous	USPAT;	2004/05/14 10:12
		or SiN or nitride) with situ)	US-PGPUB;	
			EPO; JPO;	
	* 1		DERWENT;	
			IBM TDB	
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